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Applied Surface Science 82/83 (1994) 595-601

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Author index

- Abukawa, T., see Sasaki, M. 82/83 (1994) 387
- Akamatsu, M., S. Narahara, T. Kobayashi and F. Hasegawa, Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃ 82/83 (1994) 228
- Akazawa, H., Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane 82/83 (1994) 394
- Akinaga, H. and K. Tanaka, Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy 82/83 (1994) 298
- Aleskovski, V.B., see Drozd, V.E. 82/83 (1994) 587
- Aleskovski, V.B., see Drozd, V.E. 82/83 (1994) 591
- Aono, M., see Kawai, M. 82/83 (1994) 487
- Aoyagi, Y., see Isshiki, H. 82/83 (1994) 57
- Aoyagi, Y., see Meguro, T. 82/83 (1994) 193
- Aruga, T., see Taguchi, Y. 82/83 (1994) 434
- Asahi, H., see Kim, J.H. 82/83 (1994) 76
- Asahi, H., S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda, Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy 82/83 (1994) 109
- Asami, K., see Kim, J.H. 82/83 (1994) 76
- Asami, K., see Asahi, H. 82/83 (1994) 109
- Asami, S., N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt, Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆ 82/83 (1994) 359
- Asikainen, T., M. Ritala and M. Leskelä, Growth of In₂S₃ thin films by atomic layer epitaxy 82/83 (1994) 122
- Bannerjee, S., see Asami, S. 82/83 (1994) 359
- Baraban, A.P., see Drozd, V.E. 82/83 (1994) 583
- Bedair, S.M. and N.A. El-Masry, Recent advances in atomic layer epitaxy devices 82/83 (1994) 7
- Bedair, S.M., see Hayafuji, N. 82/83 (1994) 18
- Bonser, D.J., see Asami, S. 82/83 (1994) 359
- Chan, S.-H., S.M. Sze, C.-Y. Chang and W.-I. Lee, Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources 82/83 (1994) 85
- Chang, C.-Y., see Chan, S.-H. 82/83 (1994) 85
- Choyke, W.J., see Yates, Jr., J.T. 82/83 (1994) 180
- Chub, A.B., see Khramtsova, E.A. 82/83 (1994) 576
- Colter, P.C., see Hayafuji, N. 82/83 (1994) 18
- Creighton, J.R., Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy 82/83 (1994) 171
- Daté, M., see Taguchi, Y. 82/83 (1994) 434
- DenBaars, S.P., see Keller, B.P. 82/83 (1994) 126
- Dillon, A.C., see George, S.M. 82/83 (1994) 460
- Dip, A., see Hayafuji, N. 82/83 (1994) 18
- Drozd, V.E., A.P. Baraban and I.O. Nikiforova, Electrical properties of Si-Al₂O₃ structures grown by ML-ALE 82/83 (1994) 583
- Drozd, V.E., A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov, Synthesis of oxide superalloys by ML-ALE method 82/83 (1994) 587
- Drozd, V.E. and V.B. Aleskovski, Synthesis of conducting oxides by ML-ALE 82/83 (1994) 591
- Ekerdt, J.G., see Asami, S. 82/83 (1994) 359
- El-Masry, N.A., see Bedair, S.M. 82/83 (1994) 7
- El-Masry, N.A., see Hayafuji, N. 82/83 (1994) 18
- Eldallal, G.M., see Hayafuji, N. 82/83 (1994) 18
- Elers, K.-E., M. Ritala, M. Leskelä and E. Rauhala, NbCl₅ as a precursor in atomic layer epitaxy 82/83 (1994) 468
- Enta, Y., N. Miyamoto, Y. Takakuwa and H. Kato, Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth 82/83 (1994) 327
- Fahy, M.R., K. Sato and B.A. Joyce, Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A 82/83 (1994) 14
- Fretwell, J., see Asami, S. 82/83 (1994) 359
- Fujita, K., see Hirai, M. 82/83 (1994) 23

- Furukawa, H., see Yoshida, I. 82/83 (1994) 501
 Furukawa, S., see Hwang, S.M. 82/83 (1994) 523
- Gamo, K., see Meguro, T. 82/83 (1994) 193
 Gates, S.M., see Koleske, D.D. 82/83 (1994) 344
 Ge, Q. and P.J. Møller, CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces 82/83 (1994) 305
 George, S.M., see Okada, L.A. 82/83 (1994) 410
 George, S.M., O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way, Atomic layer controlled deposition of SiO₂ and Al₂O₃ using ABAB... binary reaction sequence chemistry 82/83 (1994) 460
 Gonda, S., see Kim, J.H. 82/83 (1994) 76
 Gonda, S., see Asahi, H. 82/83 (1994) 109
 Goto, H., see Suzuki, T. 82/83 (1994) 103
 Goto, K., see Takemi, M. 82/83 (1994) 115
 Goto, S., see Ohno, H. 82/83 (1994) 164
 Gotoda, M., H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita, Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE 82/83 (1994) 80
- Hanada, T., see Kawai, M. 82/83 (1994) 487
 Hara, K., see Suzuki, T. 82/83 (1994) 103
 Hara, K., see Kano, N. 82/83 (1994) 132
 Hasegawa, F., see Akamatsu, M. 82/83 (1994) 228
 Haukka, S., E.-L. Lakomaa and T. Suntola, Surface coverage of ALE precursors on oxides 82/83 (1994) 548
 Hayafuji, N., G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair, Atomic layer epitaxy of device quality AlGaAs and AlAs 82/83 (1994) 18
 Heun, S., M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima, Morphology of epitaxial SrF₂ films on atomically modified InP(100) 82/83 (1994) 507
 Hibino, H. and T. Ogino, Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111) 82/83 (1994) 374
 Himei, H., E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto, Theoretical estimation of ordered metal species in zeolite pores 82/83 (1994) 543
 Hirabayashi, I., see Matsubara, M. 82/83 (1994) 494
 Hirai, M., H. Ohnishi, K. Fujita and T. Watanabe, Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A 82/83 (1994) 23
 Hirosawa, T., see Yoshida, I. 82/83 (1994) 501
 Hirose, S., see Kano, N. 82/83 (1994) 132
 Holmes Jr., A.L., see Keller, B.P. 82/83 (1994) 126
 Homma, Y., see Yamaguchi, H. 82/83 (1994) 223
- Hongo, S., S. Taniguchi, K. Ojima, T. Urano and T. Kanaji, Adsorption and desorption of H₂O on potassium pre-covered Si(100)2 × 1 surface 82/83 (1994) 437
 Hongo, S., K. Ojima, S. Taniguchi, T. Urano and T. Kanaji, Observation of the interface of Ba/Si(100) by MDS and TDS 82/83 (1994) 537
 Horikoshi, Y., see Yamaguchi, H. 82/83 (1994) 223
 Hübner, A., see Yates, Jr., J.T. 82/83 (1994) 180
 Hwang, S.M., A. Izumi, K. Tsutsui and S. Furukawa, Surface modification of CaF₂ in atomic layer scale by electron beam exposure 82/83 (1994) 523
- Ide, Y. and M. Yamada, Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography 82/83 (1994) 310
 Ikeda, H., Y. Miura, N. Takahashi, A. Koukitu and H. Seki, Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy 82/83 (1994) 257
 Ikeda, H., see Suda, Y. 82/83 (1994) 332
 Imai, S. and M. Matsumura, Hydrogen atom assisted ALE of silicon 82/83 (1994) 322
 Imai, S., see Sugahara, S. 82/83 (1994) 380
 Inada, T., see Kiyota, Y. 82/83 (1994) 400
 Inoue, N., see Yokoyama, H. 82/83 (1994) 158
 Ishida, M., see Suda, Y. 82/83 (1994) 332
 Ishii, M., see Meguro, T. 82/83 (1994) 193
 Isshiki, H., Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro, Surface processes of selective growth by atomic layer epitaxy 82/83 (1994) 57
 Isu, T., see Gotoda, M. 82/83 (1994) 80
 Ito, H., see Suzuki, T. 82/83 (1994) 103
 Ito, T., K. Shiraishi and T. Ohno, A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in Al_xGa_{1-x}As on a GaAs(001) surface 82/83 (1994) 208
 Iwai, S., see Isshiki, H. 82/83 (1994) 57
 Iwasa, I., see Otake, S. 82/83 (1994) 263
 Iwata, K., see Kim, J.H. 82/83 (1994) 76
 Izumi, A., see Hwang, S.M. 82/83 (1994) 523
- Jimbo, T., see Soga, T. 82/83 (1994) 64
 Joyce, B.A., see Fahy, M.R. 82/83 (1994) 14
- Kanaji, T., see Hongo, S. 82/83 (1994) 437
 Kanaji, T., see Hongo, S. 82/83 (1994) 537
 Kano, N., S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto, AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source 82/83 (1994) 132
 Katayama, I., see Ohnishi, H. 82/83 (1994) 444

- Katayama, I., see Tanaka, Y. 82/83 (1994) 528
- Katayama, M., see Kawai, M. 82/83 (1994) 487
- Katayama, Y., see Ohno, H. 82/83 (1994) 164
- Kato, H., see Enta, Y. 82/83 (1994) 327
- Kawai, M., Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville, Layer controlled growth of oxide superconductors 82/83 (1994) 487
- Kawanishi, H., see Takahashi, I. 82/83 (1994) 70
- Kawasaki, M., see Song, Z. 82/83 (1994) 250
- Keller, B.P., J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra, Flow modulation epitaxy of Ga_xIn_{1-x}As/AlAs heterostructures on InP for resonant tunneling diodes 82/83 (1994) 126
- Khrantsova, E.A., A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits, Growth of extra-thin ordered aluminum films on Si(111) surface 82/83 (1994) 576
- Kim, J.H., H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda, Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices 82/83 (1994) 76
- Kim, S.G., see Kim, J.H. 82/83 (1994) 76
- Kim, S.G., see Asahi, H. 82/83 (1994) 109
- Kimura, S., see Murakami, E. 82/83 (1994) 338
- Kimura, T., see Takemi, M. 82/83 (1994) 115
- Kitamura, T., see Sugahara, S. 82/83 (1994) 380
- Kiyota, Y., T. Nakamura and T. Inada, Boron δ -doping in Si using atmospheric pressure CVD 82/83 (1994) 400
- Kobayashi, M., see Yoshikawa, A. 82/83 (1994) 316
- Kobayashi, N. and T. Makimoto, Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs 82/83 (1994) 284
- Kobayashi, N., see Uwai, K. 82/83 (1994) 290
- Kobayashi, T., see Akamatsu, M. 82/83 (1994) 228
- Koleske, D.D. and S.M. Gates, Si ALE using chlorine/hydrogen exchange. Fundamentals and films 82/83 (1994) 344
- Komolov, S.A., see Møller, P.J. 82/83 (1994) 569
- Komura, T., see Uesugi, K. 82/83 (1994) 367
- Kono, S., see Sasaki, M. 82/83 (1994) 387
- Korol'kov, D.V., see Drozd, V.E. 82/83 (1994) 587
- Koukitu, A., see Ikeda, H. 82/83 (1994) 257
- Kubo, M., R. Yamauchi, R. Vetrivel and A. Miyamoto, Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics 82/83 (1994) 559
- Kubo, M., see Vetrivel, R. 82/83 (1994) 516
- Kubo, M., see Himei, H. 82/83 (1994) 543
- Kubota, H., M. Nagata, R. Miyagawa and M.A. Nicolet, Oxidation of TiN thin films in an ion-beam-assisted deposition process 82/83 (1994) 565
- Kujirai, H., see Murakami, E. 82/83 (1994) 338
- Kukimoto, H., see Kano, N. 82/83 (1994) 132
- Kumagai, H. and K. Toyoda, In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions 82/83 (1994) 481
- Kurabayashi, T., see Plotka, P. 82/83 (1994) 91
- Kurabayashi, T. and J. Nishizawa, Temperature synchronized molecular layer epitaxy 82/83 (1994) 97
- Lakomaa, E.-L., see Haukka, S. 82/83 (1994) 548
- Lazneva, E.F., see Møller, P.J. 82/83 (1994) 569
- Lee, W.-I., see Chan, S.-H. 82/83 (1994) 85
- Leskelä, M., see Asikainen, T. 82/83 (1994) 122
- Leskelä, M., see Niinistö, L. 82/83 (1994) 454
- Leskelä, M., see Elers, K.-E. 82/83 (1994) 468
- Leskelä, M., see Rautanen, J. 82/83 (1994) 553
- Lifshits, V.G., see Khrantsova, E.A. 82/83 (1994) 576
- Liu, Z.-Y., see Kawai, M. 82/83 (1994) 487
- Lucas, S.R., see Yates, Jr., J.T. 82/83 (1994) 180
- Lujala, V., J. Skarp, M. Tammenmaa and T. Suntola, Atomic layer epitaxy growth of doped zinc oxide thin films from organometals 82/83 (1994) 34
- Maeda, F., see Watanabe, Y. 82/83 (1994) 136
- Maeda, F., Y. Watanabe and M. Oshima, Surface reactions of Ga and As on Sb-terminated GaAs(001) 82/83 (1994) 276
- Maeda, H., see Nakayama, H. 82/83 (1994) 214
- Maeda, Y., see Watamori, M. 82/83 (1994) 417
- Maeyama, S., see Heun, S. 82/83 (1994) 507
- Mahajan, A., see Asami, S. 82/83 (1994) 359
- Makimoto, T., see Kobayashi, N. 82/83 (1994) 284
- Maruno, S., see Gotoda, M. 82/83 (1994) 80
- Maruya, E., see Himei, H. 82/83 (1994) 543
- Matsubara, M. and I. Hirabayashi, Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition 82/83 (1994) 494
- Matsumiya, Y., see Sakuma, Y. 82/83 (1994) 46
- Matsumura, M., see Imai, S. 82/83 (1994) 322
- Matsumura, M., see Sugahara, S. 82/83 (1994) 380
- Matsuura, T., see Suzue, K. 82/83 (1994) 422
- McConville, C.F., see Kawai, M. 82/83 (1994) 487
- Meguro, T., see Isshiki, H. 82/83 (1994) 57
- Meguro, T., M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi, Control of the etching reaction of digital etching using tunable UV laser irradiation 82/83 (1994) 193
- Mihashi, Y., see Takemi, M. 82/83 (1994) 115
- Mishra, U.K., see Keller, B.P. 82/83 (1994) 126
- Miura, Y., see Ikeda, H. 82/83 (1994) 257
- Miyagawa, R., see Kubota, H. 82/83 (1994) 565
- Miyamoto, A., see Vetrivel, R. 82/83 (1994) 516
- Miyamoto, A., see Himei, H. 82/83 (1994) 543
- Miyamoto, A., see Kubo, M. 82/83 (1994) 559

- Miyamoto, N., see Enta, Y. 82/83 (1994) 327
 Miyamoto, N., see Suemitsu, M. 82/83 (1994) 449
 Mochizuki, Y., T. Takada and A. Usui, Theoretical studies on the chloride ALE process 82/83 (1994) 200
 Møller, P.J., see Ge, Q. 82/83 (1994) 305
 Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001) 82/83 (1994) 569
 Mori, K., see Takemi, M. 82/83 (1994) 115
 Morioka, H., see Watamori, M. 82/83 (1994) 417
 Morishita, H., see Tanaka, Y. 82/83 (1994) 528
 Morishita, Y., see Ohno, H. 82/83 (1994) 164
 Munekata, H., see Kano, N. 82/83 (1994) 132
 Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces 82/83 (1994) 338
 Murota, J., see Sakuraba, M. 82/83 (1994) 354
 Murota, J., see Suzue, K. 82/83 (1994) 422
 Muto, S., see Sakuma, Y. 82/83 (1994) 46
 Muto, S., see Sakuma, Y. 82/83 (1994) 239

 Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH₂Cl₂ and C₂H₂ 82/83 (1994) 405
 Nagata, M., see Kubota, H. 82/83 (1994) 565
 Naitoh, M., see Watamori, M. 82/83 (1994) 417
 Nakaji, M., see Takahashi, I. 82/83 (1994) 70
 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46
 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239
 Nakamura, T., see Kiyota, Y. 82/83 (1994) 400
 Nakao, M., see Yoshida, I. 82/83 (1994) 501
 Nakayama, H., M. Tochigi, H. Maeda and T. Nishino, Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors 82/83 (1994) 214
 Nakazawa, H., see Suemitsu, M. 82/83 (1994) 449
 Narahara, S., see Akamatsu, M. 82/83 (1994) 228
 Nicolet, M.A., see Kubota, H. 82/83 (1994) 565
 Niinistö, L. and M. Leskelä, Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications 82/83 (1994) 454
 Niinistö, L., see Rautanen, J. 82/83 (1994) 553
 Nikiforova, I.O., see Drozd, V.E. 82/83 (1994) 583
 Nishijima, M., see Taguchi, Y. 82/83 (1994) 434
 Nishinaga, T. and X.Q. Shen, Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE 82/83 (1994) 141
 Nishino, T., see Nakayama, H. 82/83 (1994) 214
 Nishizawa, J., Molecular layer epitaxy of GaAs 82/83 (1994) 1
 Nishizawa, J., see Oyama, Y. 82/83 (1994) 41

 Nishizawa, J., see Plotka, P. 82/83 (1994) 91
 Nishizawa, J., see Kurabayashi, T. 82/83 (1994) 97
 Nomura, Y., see Ohno, H. 82/83 (1994) 164
 Nunoshita, M., see Gotoda, M. 82/83 (1994) 80
 Nykänen, E., see Rautanen, J. 82/83 (1994) 553

 Ogino, T., see Hibino, H. 82/83 (1994) 374
 Ogura, T., see Asahi, H. 82/83 (1994) 109
 Ohba, Y., see Ohnishi, H. 82/83 (1994) 444
 Ohmi, T., see Suzue, K. 82/83 (1994) 422
 Ohnishi, H., see Hirai, M. 82/83 (1994) 23
 Ohnishi, H., Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura, Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures 82/83 (1994) 444
 Ohno, H., S. Goto, Y. Nomura, Y. Morishita and Y. Katayama, Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium 82/83 (1994) 164
 Ohno, T., see Ito, T. 82/83 (1994) 208
 Ohta, T., see Vetrivel, R. 82/83 (1994) 516
 Ohtsuka, N., see Sakuma, Y. 82/83 (1994) 46
 Ohtsuka, N., see Ozeki, M. 82/83 (1994) 233
 Ojima, K., see Hongo, S. 82/83 (1994) 437
 Ojima, K., see Hongo, S. 82/83 (1994) 537
 Okada, L.A., M.L. Wise and S.M. George, Isothermal H₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors 82/83 (1994) 410
 Okada, L.A., see George, S.M. 82/83 (1994) 460
 Ono, S., see Sakuraba, M. 82/83 (1994) 354
 Oshima, M., see Watanabe, Y. 82/83 (1994) 136
 Oshima, M., see Maeda, F. 82/83 (1994) 276
 Oshima, M., see Heun, S. 82/83 (1994) 507
 Otake, S., A. Sakamoto, M. Yamamoto and I. Iwasa, In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages 82/83 (1994) 263
 Ott, A.W., see George, S.M. 82/83 (1994) 460
 Oura, K., see Watamori, M. 82/83 (1994) 417
 Oura, K., see Ohnishi, H. 82/83 (1994) 444
 Oura, K., see Tanaka, Y. 82/83 (1994) 528
 Oyama, Y., P. Plotka and J. Nishizawa, Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application 82/83 (1994) 41
 Oyama, Y., see Plotka, P. 82/83 (1994) 91
 Ozeki, M., see Sakuma, Y. 82/83 (1994) 46
 Ozeki, M. and N. Ohtsuka, Atomic layer epitaxy of AlAs: growth mechanism 82/83 (1994) 233

 Partlow, W.D., see Yates, Jr., J.T. 82/83 (1994) 180
 Plotka, P., T. Kurabayashi, Y. Oyama and J. Nishizawa, Ideal static induc-

- tion transistor implemented with molecular layer epitaxy 82/83 (1994) 91
- Plotka, P., see Oyama, Y. 82/83 (1994) 41
- Rauhala, E., see Elers, K.-E. 82/83 (1994) 468
- Rautanen, J., M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen, The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy 82/83 (1994) 553
- Ritala, M., see Asikainen, T. 82/83 (1994) 122
- Ritala, M., see Elers, K.-E. 82/83 (1994) 468
- Russell, N.M., see Asami, S. 82/83 (1994) 359
- Ryzhkov, S.V., see Khramtsova, E.A. 82/83 (1994) 576
- Sakamoto, A., see Otake, S. 82/83 (1994) 263
- Sakuma, Y., M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama, Pulsed-jet epitaxy: application to device processes 82/83 (1994) 46
- Sakuma, Y., S. Muto, K. Nakajima and N. Yokoyama, A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy 82/83 (1994) 239
- Sakuraba, M., J. Murota, T. Watanabe, Y. Sawada and S. Ono, Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases 82/83 (1994) 354
- Saranin, A.A., see Khramtsova, E.A. 82/83 (1994) 576
- Sasaki, M., see Yoshida, S. 82/83 (1994) 28
- Sasaki, M. and S. Yoshida, Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces 82/83 (1994) 269
- Sasaki, M., T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono, Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001) 82/83 (1994) 387
- Sasaoka, C. and A. Usui, Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces 82/83 (1994) 348
- Sato, K., see Fahy, M.R. 82/83 (1994) 14
- Sato, M., Surface structure dependence of O₂-W adsorption system 82/83 (1994) 532
- Sato, S., see Sasaki, M. 82/83 (1994) 387
- Sawada, Y., see Sakuraba, M. 82/83 (1994) 354
- Sawada, Y., see Suzue, K. 82/83 (1994) 422
- Sawaki, N., see Suzuki, T. 82/83 (1994) 103
- Schaefer, J., see Yates, Jr., J.T. 82/83 (1994) 180
- Seki, H., see Ikeda, H. 82/83 (1994) 257
- Seo, A. and H. Shindo, Atomic force microscopic study of directional SrSO₄(001) surface and its etching property 82/83 (1994) 475
- Seta, M., see Asahi, H. 82/83 (1994) 109
- Shen, X.Q., see Nishinaga, T. 82/83 (1994) 141
- Shigematsu, H., see Sakuma, Y. 82/83 (1994) 46
- Shindo, H., see Seo, A. 82/83 (1994) 475
- Shinohara, M., see Yokoyama, H. 82/83 (1994) 158
- Shiraishi, K., see Ito, T. 82/83 (1994) 208
- Shogen, S., see Song, Z. 82/83 (1994) 250
- Skarp, J., see Lujala, V. 82/83 (1994) 34
- Sneh, O., see George, S.M. 82/83 (1994) 460
- Soga, T., T. Jimbo and M. Umeno, Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition 82/83 (1994) 64
- Soininen, P., see Rautanen, J. 82/83 (1994) 553
- Song, Z., S. Shogen, M. Kawasaki and I. Suemune, X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution 82/83 (1994) 250
- Steiner IV, P.A., see Asami, S. 82/83 (1994) 359
- Suda, Y., M. Ishida, M. Yamashita and H. Ikeda, Sub-atomic-layer epitaxy of Si using Si₂H₆ 82/83 (1994) 332
- Suemitsu, M., H. Nakazawa and N. Miyamoto, Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1 82/83 (1994) 449
- Suemune, I., Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs 82/83 (1994) 149
- Suemune, I., see Song, Z. 82/83 (1994) 250
- Sugahara, S., T. Kitamura, S. Imai and M. Matsumura, Atomic layer epitaxy of germanium 82/83 (1994) 380
- Sugano, T., see Isshiki, H. 82/83 (1994) 57
- Sugano, T., see Meguro, T. 82/83 (1994) 193
- Sugimoto, H., see Gotoda, M. 82/83 (1994) 80
- Sugiyama, M., see Heun, S. 82/83 (1994) 507
- Suntola, T., see Lujala, V. 82/83 (1994) 34
- Suntola, T., see Haukka, S. 82/83 (1994) 548
- Susaki, W., see Gotoda, M. 82/83 (1994) 80
- Suzue, K., T. Matsuura, J. Murota, Y. Sawada and T. Ohmi, Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar⁺ irradiation 82/83 (1994) 422
- Suzuki, S., see Sasaki, M. 82/83 (1994) 387
- Suzuki, T., H. Goto, N. Sawaki, H. Ito and K. Hara, Autocompensation in Si planar doped GaAs 82/83 (1994) 103
- Sze, S.M., see Chan, S.-H. 82/83 (1994) 85
- Taguchi, Y., M. Daté, N. Takagi, T. Aruga and M. Nishijima, Chemical reactivity of the Si(111)($\sqrt{3} \times \sqrt{3}$)

- R30°-B surface: an electron-energy-loss spectroscopy study 82/83 (1994) 434
- Takada, T., see Mochizuki, Y. 82/83 (1994) 200
- Takagi, N., see Taguchi, Y. 82/83 (1994) 434
- Takahashi, I., M. Nakaji and H. Kawanishi, Migration and related buried epitaxy using digital epitaxial growth conditions 82/83 (1994) 70
- Takahashi, N., see Ikeda, H. 82/83 (1994) 257
- Takakuwa, Y., see Enta, Y. 82/83 (1994) 327
- Takamiya, S., see Takemi, M. 82/83 (1994) 115
- Takemi, M., T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya, Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction 82/83 (1994) 115
- Takiguchi, T., K. Uesugi, M. Yoshimura and T. Yao, Atomic-scale modification of the AlCl₃-adsorbed Si(111)-7 × 7 surface 82/83 (1994) 428
- Tammenmaa, M., see Lujala, V. 82/83 (1994) 34
- Tanaka, K., see Akinaga, H. 82/83 (1994) 298
- Tanaka, Y., H. Morishita, M. Watamori, K. Oura and I. Katayama, Structural study of SrTiO₃(100) surfaces by low energy ion scattering 82/83 (1994) 528
- Taniguchi, S., see Hongo, S. 82/83 (1994) 437
- Taniguchi, S., see Hongo, S. 82/83 (1994) 537
- Tanimoto, M., see Yokoyama, H. 82/83 (1994) 158
- Tasch, A., see Asami, S. 82/83 (1994) 359
- Tochigi, M., see Nakayama, H. 82/83 (1994) 214
- Tokita, S., see Yoshikawa, A. 82/83 (1994) 316
- Toyoda, K., see Kumagai, H. 82/83 (1994) 481
- Tsutsui, K., see Hwang, S.M. 82/83 (1994) 523
- Tulub, A.A., see Drozd, V.E. 82/83 (1994) 587
- Ueda, O., see Sakuma, Y. 82/83 (1994) 46
- Uesugi, K., T. Komura, M. Yoshimura and T. Yao, Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates 82/83 (1994) 367
- Uesugi, K., see Takiguchi, T. 82/83 (1994) 428
- Umeno, M., see Soga, T. 82/83 (1994) 64
- Urano, T., see Hongo, S. 82/83 (1994) 437
- Urano, T., see Hongo, S. 82/83 (1994) 537
- Usui, A., see Mochizuki, Y. 82/83 (1994) 200
- Usui, A., see Sasaoka, C. 82/83 (1994) 348
- Utriainen, M., see Rautanen, J. 82/83 (1994) 553
- Uwai, K. and N. Kobayashi, Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption 82/83 (1994) 290
- Vetrivel, R., R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta, Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations 82/83 (1994) 516
- Vetrivel, R., see Himeji, H. 82/83 (1994) 543
- Vetrivel, R., see Kubo, M. 82/83 (1994) 559
- Watamori, M., M. Naitoh, H. Morioka, Y. Maeda and K. Oura, Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis 82/83 (1994) 417
- Watamori, M., see Tanaka, Y. 82/83 (1994) 528
- Watanabe, H., see Asahi, H. 82/83 (1994) 109
- Watanabe, T., see Hirai, M. 82/83 (1994) 23
- Watanabe, T., see Sakuraba, M. 82/83 (1994) 354
- Watanabe, Y., F. Maeda and M. Oshima, Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001) 82/83 (1994) 136
- Watanabe, Y., see Maeda, F. 82/83 (1994) 276
- Watanabe, Y., see Heun, S. 82/83 (1994) 507
- Way, J.D., see George, S.M. 82/83 (1994) 460
- White, J.M., see Asami, S. 82/83 (1994) 359
- Wise, M.L., see Okada, L.A. 82/83 (1994) 410
- Wise, M.L., see George, S.M. 82/83 (1994) 460
- Yamada, M., see Ide, Y. 82/83 (1994) 310
- Yamada, M., see Sasaki, M. 82/83 (1994) 387
- Yamaguchi, H., Y. Homma and Y. Horikoshi, In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy 82/83 (1994) 223
- Yamaguchi, Y., see Nagasawa, H. 82/83 (1994) 405
- Yamamoto, M., see Otake, S. 82/83 (1994) 263
- Yamamoto, Y., see Ohnishi, H. 82/83 (1994) 444
- Yamano, H., see Vetrivel, R. 82/83 (1994) 516
- Yamashita, M., see Suda, Y. 82/83 (1994) 332
- Yamauchi, R., see Vetrivel, R. 82/83 (1994) 516
- Yamauchi, R., see Kubo, M. 82/83 (1994) 559
- Yao, T., see Uesugi, K. 82/83 (1994) 367
- Yao, T., see Takiguchi, T. 82/83 (1994) 428
- Yates, Jr., J.T., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke, Activation of the Ga-CH₃ bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels 82/83 (1994) 180
- Yen, J.C., see Keller, B.P. 82/83 (1994) 126
- Yeom, H.W., see Sasaki, M. 82/83 (1994) 387
- Yokoyama, H., M. Tanimoto, M. Shinohara and N. Inoue, Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy 82/83 (1994) 158

- | | | | |
|--|------------------|---|------------------|
| Yokoyama, N., see Sakuma, Y. | 82/83 (1994) 46 | Yoshida, S., see Sasaki, M. | 82/83 (1994) 269 |
| Yokoyama, N., see Sakuma, Y. | 82/83 (1994) 239 | Yoshikawa, A., M. Kobayashi and S. Tokita, Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method | 82/83 (1994) 316 |
| Yoshida, I., H. Furukawa, T. Hirosawa and M. Nakao, Fabrication of CuO ₂ -plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy | 82/83 (1994) 501 | Yoshimura, M., see Uesugi, K. | 82/83 (1994) 367 |
| Yoshida, S. and M. Sasaki, Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE | 82/83 (1994) 28 | Yoshimura, M., see Takiguchi, T. | 82/83 (1994) 428 |
| | | Yoshino, J., see Kano, N. | 82/83 (1994) 132 |
| | | Zotov, A.V., see Khramtsova, E.A. | 82/83 (1994) 576 |



ELSEVIER

Applied Surface Science 82/83 (1994) 602-621

applied
surface science

Subject index

Alkali metals

- Adsorption and desorption of H₂O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553

Alloys

- Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587

Aluminium

- Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta,

- K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Flow modulation epitaxy of Ga_xIn_{1-x}As/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
- A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in Al_xGa_{1-x}As on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Maki-moto 82/83 (1994) 284
- Atomic-scale modification of the AlCl₃-adsorbed Si(111)-7 × 7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516

Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits

82/83 (1994) 576

Aluminium oxide

Atomic layer controlled deposition of SiO₂ and Al₂O₃ using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way

82/83 (1994) 460

In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda

82/83 (1994) 481

Electrical properties of Si–Al₂O₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova

82/83 (1994) 583

Ammonia

Chemical reactivity of the Si(111)-(√3 × √3)R30°-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima

82/83 (1994) 434

Antimony

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda

82/83 (1994) 109

Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima

82/83 (1994) 276

Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura

82/83 (1994) 338

Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono

82/83 (1994) 387

Argon

Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-en-

ergy Ar⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi

82/83 (1994) 422

Arsenic

AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto

82/83 (1994) 132

Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune

82/83 (1994) 149

Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka

82/83 (1994) 233

Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki

82/83 (1994) 257

Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida

82/83 (1994) 269

Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima

82/83 (1994) 276

Atomic force microscopy

Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue

82/83 (1994) 158

X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune

82/83 (1994) 250

Atomic force microscopic study of directional SrSO₄(001) surface and its etching property, A. Seo and H. Shindo

82/83 (1994) 475

Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi

82/83 (1994) 494

Morphology of epitaxial SrF₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima

82/83 (1994) 507

The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen

82/83 (1994) 553

Auger electron spectroscopy

- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
- Activation of the Ga-CH₃ bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576

Barium

- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537

Boron

- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400

Cadmium selenide

- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316

Calcium

- Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523

Carbon

- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Maki-moto 82/83 (1994) 284

Carbon dioxide

- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569

Carbon monoxide

- CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569

Chemical vapour deposition

- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
- Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethyl-

- gallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
- A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
- Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
- In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
- Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
- Sub-atomic-layer epitaxy of Si using Si₂H₆, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Mechanisms of SiC growth by alternate supply of SiH₂Cl₂ and C₂H₂, H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
- Isothermal H₂ desorption kinetics from Si(100)2 \times 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- Atomic layer controlled deposition of SiO₂ and Al₂O₃ using ABAB... bi-

- nary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- ### Clusters
- Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559
- ### Computer simulations
- Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
- ### Copper
- CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- ### Deuterium
- Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1, M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449
- ### Doping effects
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and Al-GaAs, N. Kobayashi and T. Maki-moto 82/83 (1994) 284
- Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- ### Elastic recoil detection
- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
- ### Electrical properties
- Ideal static induction transistor implemented with molecular layer epitaxy, P. Plotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
- Flow modulation epitaxy of Ga_xIn_{1-x}As/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Electrical properties of Si-Al₂O₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583

Electron bombardment

- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310

Electron diffraction

- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Sub-atomic-layer epitaxy of Si using Si₂H₆, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
- Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirokawa and M. Nakao 82/83 (1994) 501

Electron energy loss spectroscopy

- Chemical reactivity of the Si(111)-($\sqrt{3} \times \sqrt{3}$)R30°-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569

Electron microscopy

- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494

Ellipsometry

- In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
- Synthesis of oxide superalloys by MLE method, V.E. Drozd, A.A. Tulyub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587

Epitaxy

- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Ideal static induction transistor implemented with molecular layer epitaxy, P. Plotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
- Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Flow modulation epitaxy of Ga_xIn_{1-x}As/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
- Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164

- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
- A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
- Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
- Sub-atomic-layer epitaxy of Si using Si₂H₆, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Mechanisms of SiC growth by alternate supply of SiH₂Cl₂ and C₂H₂, H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
- Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirose and M. Nakao 82/83 (1994) 501
- Morphology of epitaxial SrF₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Electrical properties of Si-Al₂O₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583

Etching

- Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
- X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422

Field electron microscopy

- Surface structure dependence of O_2 -W adsorption system, M. Sato 82/83 (1994) 532

Gallium

- Activation of the Ga- CH_3 bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276

Gallium arsenide

- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23

- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Ideal static induction transistor implemented with molecular layer epitaxy, P. Plotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
- Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{AlAs}$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
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- Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
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- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 , M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
- X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
- In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
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- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mech-

- anism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310

Gallium phosphide

- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
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Germanium

- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387

Halogenides

- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 , M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic-scale modification of the AlCl_3 -adsorbed Si(111)- 7×7 surface, T.

- Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Morphology of epitaxial SrF₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523

Halogens

- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422

Hydrides

- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228

Hydrogen

- Activation of the Ga-CH₃ bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
- Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338

- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Isothermal H₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417

Indium

- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122

Indium antimonide

- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

Indium arsenide

- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223

Indium phosphide

- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{AlAs}$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507

Infrared spectroscopy

- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
- Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548

Interfaces

- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115

- Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537

Ion bombardment

- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565

Ion scattering

- Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- NbCl_5 as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
- Structural study of $\text{SrTiO}_3(100)$ surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548

Laser processing

- Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193

Low energy electron diffraction

- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417

- Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
- Structural study of $\text{SrTiO}_3(100)$ surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from $\text{ZnO}(0001)$, P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Growth of extra-thin ordered aluminum films on $\text{Si}(111)$ surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576

Luminescence

- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{AlAs}$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- Electrical properties of $\text{Si}-\text{Al}_2\text{O}_3$ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583

Magnesium oxide

- Formation processes of ultrafine metal particles on $\text{MgO}(100)$ as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559

Mass spectroscopy

- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41

- Activation of the $\text{Ga}-\text{CH}_3$ bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from $\text{ZnO}(0001)$, P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569

Metals

- Formation processes of ultrafine metal particles on $\text{MgO}(100)$ as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559

Molecular dynamics

- Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
- Formation processes of ultrafine metal particles on $\text{MgO}(100)$ as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559

Monte Carlo simulations

- A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ on a $\text{GaAs}(001)$ surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208

Niobium

- NbCl_5 as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468

Nitrides

- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28

Optical properties

- Growth temperature dependence of optical properties of gas source MBE

- grown GaP/AIP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Organometallic vapour deposition**
- Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548
- Electrical properties of Si-Al₂O₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
- Synthesis of conducting oxides by ML-ALE, V.E. Drozd and V.B. Aleskovski 82/83 (1994) 591
- Oxides**
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
- Structural study of SrTiO₃(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
- Synthesis of conducting oxides by ML-ALE, V.E. Drozd and V.B. Aleskovski 82/83 (1994) 591
- Oxygen**
- Surface structure dependence of O₂-W adsorption system, M. Sato 82/83 (1994) 532
- Phase transitions**
- In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223

Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka

82/83 (1994) 233

Phosphorus

Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki

82/83 (1994) 257

Photochemistry

Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa

82/83 (1994) 41

Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa

82/83 (1994) 394

Photoelectron spectroscopy

Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa

82/83 (1994) 41

Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima

82/83 (1994) 136

X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune

82/83 (1994) 250

Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima

82/83 (1994) 276

Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada

82/83 (1994) 310

Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato

82/83 (1994) 327

Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono

82/83 (1994) 354

Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono

82/83 (1994) 387

Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi

82/83 (1994) 422

Morphology of epitaxial SrF₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima

82/83 (1994) 507

Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa

82/83 (1994) 523

Synthesis of oxide superalloys by MLE method, V.E. Drozd, A.A. Tullub, V.B. Aleskovski and D.V. Korol'kov

82/83 (1994) 587

Quantum effects

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda

82/83 (1994) 109

Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya

82/83 (1994) 115

Radiation damage

Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa

82/83 (1994) 523

Scanning tunneling microscopy

Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao

82/83 (1994) 367

Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino

82/83 (1994) 374

Atomic-scale modification of the AlCl₃-adsorbed Si(111)-7 × 7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao

82/83 (1994) 428

- Scanning tunneling microscope observations of Si(111) 3×1 -Ag and 6×1 -Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444

Secondary ion mass spectrometry

- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400

Selenium

- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316

Semiconductors

- Activation of the Ga-CH₃ bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214

Silane

- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354

- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Isothermal H₂ desorption kinetics from Si(100) 2×1 : dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410

Silicon

- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
- Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
- Sub-atomic-layer epitaxy of Si using Si₂H₆, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon

- substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
- Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Isothermal H_2 desorption kinetics from Si(100) 2×1 : dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Atomic-scale modification of the $AlCl_3$ -adsorbed Si(111)- 7×7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- Chemical reactivity of the Si(111)-($\sqrt{3} \times \sqrt{3}$) $R30^\circ$ -B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434
- Adsorption and desorption of H_2O on potassium precovered Si(100) 2×1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
- Scanning tunneling microscope observations of Si(111) 3×1 -Ag and 6×1 -Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444
- Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100) 2×1 , M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449
- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
- Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
- Electrical properties of Si- Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
- ### Silicon carbide
- Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2 , H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
- ### Silicon oxide
- Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
- ### Silver
- Scanning tunneling microscope observations of Si(111) 3×1 -Ag and 6×1 -Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444
- ### Sputter deposition
- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565
- ### Strontium
- Atomic force microscopic study of directional $SrSO_4(001)$ surface and its etching property, A. Seo and H. Shindo 82/83 (1994) 475
- Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Structural study of $SrTiO_3(100)$ surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- ### Sulphides
- Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122

The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen

82/83 (1994) 553

Sulphur

Atomic force microscopic study of directional $\text{SrSO}_4(001)$ surface and its etching property, A. Seo and H. Shindo

82/83 (1994) 475

Superconductivity

Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville

82/83 (1994) 487

Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi

82/83 (1994) 494

Fabrication of CuO_2 -plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirokawa and M. Nakao

82/83 (1994) 501

Superlattices

Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama

82/83 (1994) 46

Growth temperature dependence of optical properties of gas source MBE grown GaP/AIP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda

82/83 (1994) 76

Fabrication of CuO_2 -plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirokawa and M. Nakao

82/83 (1994) 501

Surface composition

Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton

82/83 (1994) 171

Surface diffusion

Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen

82/83 (1994) 141

Thermal desorption

Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune

82/83 (1994) 149

Activation of the Ga- CH_3 bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke

82/83 (1994) 180

CO adsorption on clean and atomic-layer-Cu-covered $\text{ZnO}(10\bar{1}0)$ surfaces, Q. Ge and P.J. Møller

82/83 (1994) 305

Self-limiting adsorption of thermally cracked SiCl_2H_2 on Si surfaces, C. Sasaoka and A. Usui

82/83 (1994) 348

Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt

82/83 (1994) 359

Isothermal H_2 desorption kinetics from $\text{Si}(100)2 \times 1$: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George

82/83 (1994) 410

Adsorption and desorption of H_2O on potassium precovered $\text{Si}(100)2 \times 1$ surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji

82/83 (1994) 437

Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto $\text{Si}(100)2 \times 1$, M. Suemitsu, H. Nakazawa and N. Miyamoto

82/83 (1994) 449

Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji

82/83 (1994) 537

Thin films

Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry

82/83 (1994) 7

Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola

82/83 (1994) 34

- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565

Time of flight techniques

- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269

Titanium

- Structural study of SrTiO₃(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528

Titanium nitride

- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565

Tungsten

- Surface structure dependence of O₂-W adsorption system, M. Sato 82/83 (1994) 532

Water

- Adsorption and desorption of H₂O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437

X-ray diffraction

- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirokawa and M. Nakao 82/83 (1994) 501
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553

X-ray fluorescence

- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553

X-ray spectroscopy

- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494

Zeolites

- Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543

Zinc

- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical

- probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316

Zinc oxide

- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammema and T. Suntola 82/83 (1994) 34
- CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569

